

L Number	Hits	Search Text	DB	Time stamp
1	12653	fns or ((fowler adj Nordheim) near2 stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 23:17
2	2538	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 23:20
3	4	(fns or ((fowler adj Nordheim) near2 stress)) same (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 23:21
4	0	(fns or ((fowler adj Nordheim) near2 stress)) near5 (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 23:21
5	2	(fns or ((fowler adj Nordheim) near2 stress)) near10 (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 23:21
-	12368	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:15
-	0	((gate near3 insulat\$4) same (anneal\$3 or heat\$3)) near5 vaccuum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:15
-	0	((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vaccuum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:15
-	0	((sio or (silicon near2 oxide)) and (anneal\$3 or heat\$3)) near5 vaccuum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 22:01
-	12368	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:13
-	112	((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:17
-	6	((gate near3 insulat\$4) same (anneal\$3 or heat\$3)) near5 vacuum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:15

-	5	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:19
-	1353	(poly near2 crystall\$8) same (poly near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 16:32
-	455320	tft or (thin near2 film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:21
-	275	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:22
-	291495	(anneal\$3 or heat\$3) same (vacuum or (low near2 pressure))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:29
-	275	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:38
-	54	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film)) and ((anneal\$3 or heat\$3) same (vacuum or (low near2 pressure)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:24
-	249811	(anneal\$3 or heat\$3) same (vacuum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:36
-	27	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film)) and ((anneal\$3 or heat\$3) same (vacuum))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:30
-	58093	(anneal\$3 or heat\$3) near3 (vacuum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:39
-	10	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film)) and ((anneal\$3 or heat\$3) near3 (vacuum))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:37
-	605	((poly near2 crystall\$8) same (poly near2 silicon)) and (tft or (thin near2 film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:38
-	5134	((anneal\$3 or heat\$3) near3 (vacuum)) same insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:50

-	2991	((anneal\$3 or heat\$3) near3 (vacuum)) near5 insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:51
-	1	((anneal\$3 or heat\$3) near3 (vacuum)) near5 insulat\$3) and (((poly near2 crystall\$8) same (poly near2 silicon)) and (tft or (thin near2 film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:50
-	9	((anneal\$3 or heat\$3) near3 (vacuum)) near5 (gate near3 insulat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:51
-	3613	(anneal\$3 or heat\$3) near4 (insulat\$3 or (gate near2 insulat\$3)) near4 vacuum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 16:32
-	1353	(poly near2 crystall\$8) same (poly near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 16:32
-	2	((anneal\$3 or heat\$3) near4 (insulat\$3 or (gate near2 insulat\$3)) near4 vacuum) and ((poly near2 crystall\$8) same (poly near2 silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 16:33
-	12423	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:15
-	2538	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 23:20
-	412	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and ((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:17
-	124905	vacuum near5 chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:18
-	12653	fns or ((fowler adj Nordheim) near2 stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 23:17
-	69	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and ((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (vacuum near5 chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:19

-	1	(((((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (vacuum near5 chamber)) and (fns or ((fowler adj Nordheim) near2 stress))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:19
-	3	(((((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (fns or ((fowler adj Nordheim) near2 stress))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:20
-	212	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:21
-	3	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber)) and (fns or ((fowler adj Nordheim) near2 stress))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:21
-	0	6638876.URPN.	USPAT	2004/07/27 19:23
-	24	("4585492" "5210056" "5578848" "5880040" "6020024" "6121130" "6136725" "6165834" "6168980" "6177363" "6191011" "6258690" "6274454" "6287897" "6291867" "6300203" "6306742" "6326231" "6326258" "6333557" "6335049" "6337289" "6338996" "6451713").PN.	USPAT USPAT	2004/07/27 19:23
-	3	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and (((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:25
-	4	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and vacuum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 19:26
-	39	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 20:08
-	211701	sio or (silicon near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 20:08
-	29	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and (sio or (silicon near2 oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 20:08

-	529	((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 20:24
-	50	(fns or (fowler adj Nordheim)) near2 stress	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 20:25
-	1	((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and vacuum) and (fns or ((fowler adj Nordheim) near2 stress))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 20:26
-	13	((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 20:30
-	132	((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and vacuum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 20:40